



# PHPT61002NYC

100V, 2 A NPN high power bipolar transistor

9 January 2014

Product data sheet

## 1. General description

NPN high power bipolar transistor in a SOT669 (LFPK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61002PYC

## 2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation

## 3. Applications

- Load switch
- Power management
- Linear mode voltage regulator
- Backlighting applications

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	100	V
$I_C$	collector current		-	-	2	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	6	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 2$ A; $I_B = 200$ mA; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C	-	80	150	m $\Omega$

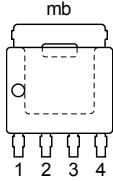
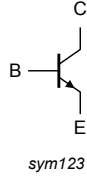


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p>LFPAK56; Power-SO8 (SOT669)</p>	
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT61002NYC	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61002NYC	1002NCA

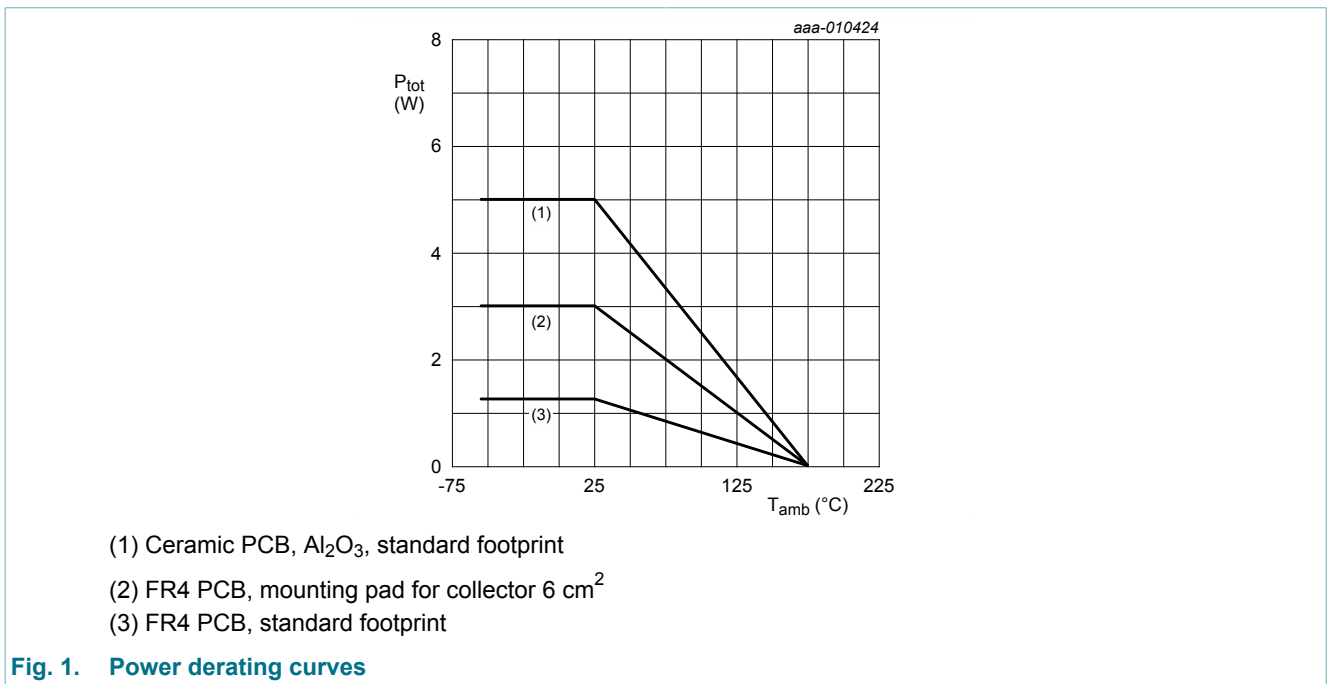
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	100	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	2	A
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	6	A
I <sub>B</sub>	base current			-	0.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic PCB; Al<sub>2</sub>O<sub>3</sub>; standard footprint.
- [4] Power dissipation from junction to mounting base.



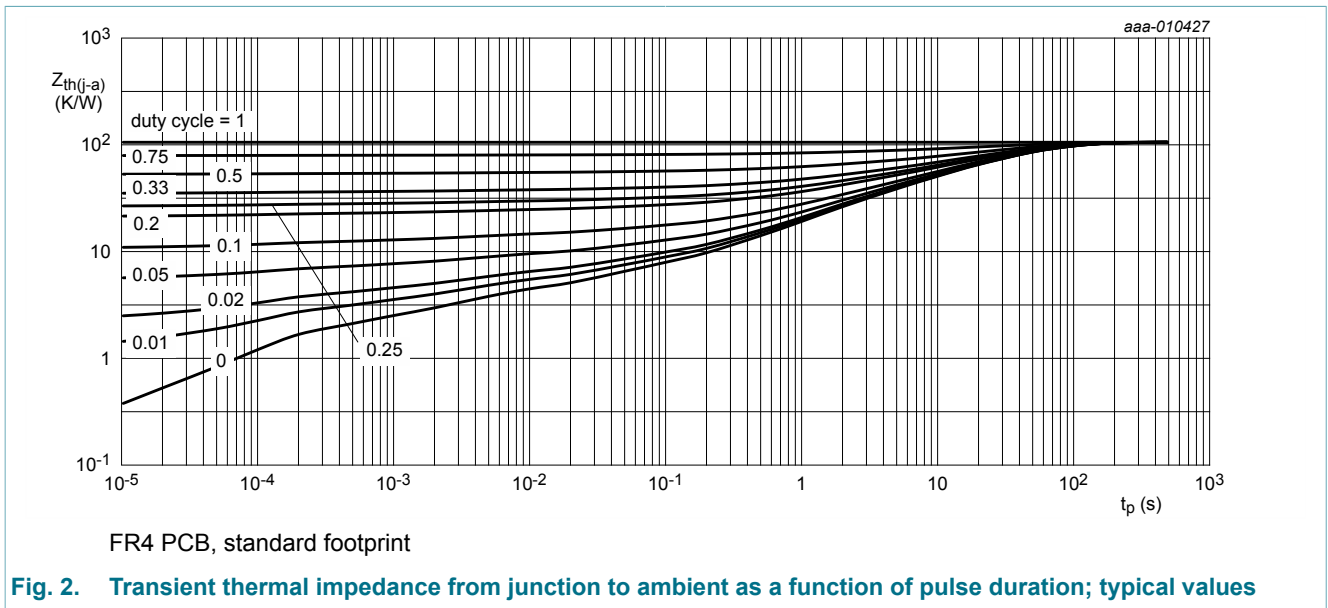
**Fig. 1. Power derating curves**

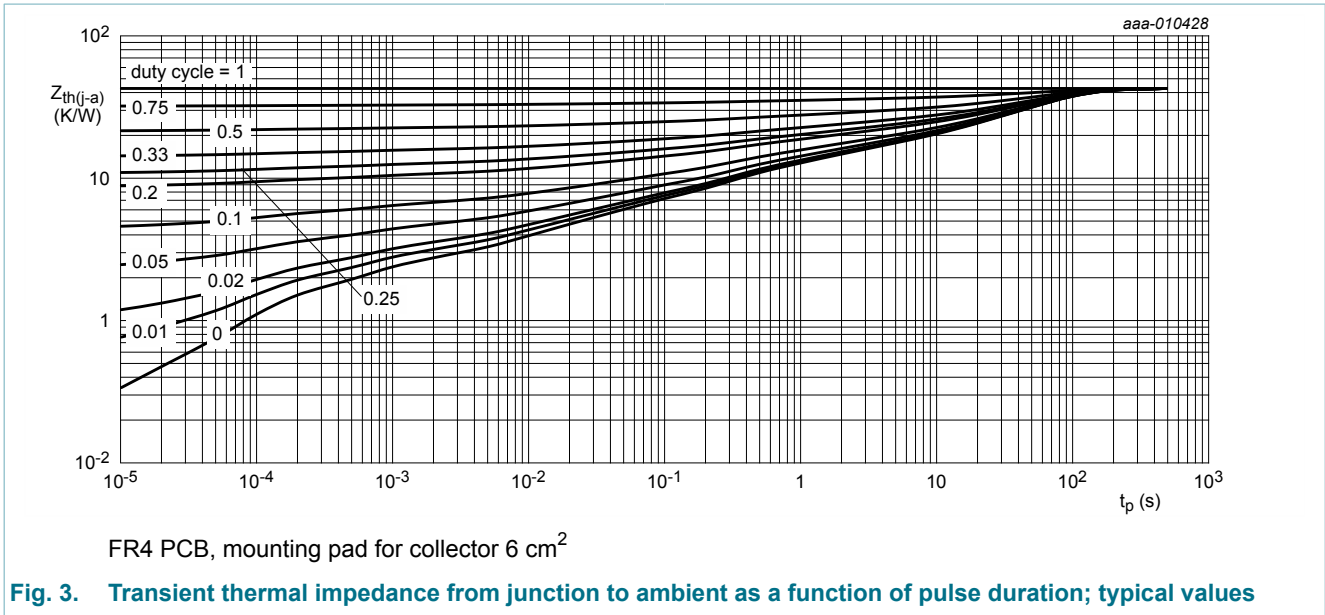
## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	50	K/W
			[3]	-	-	30	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

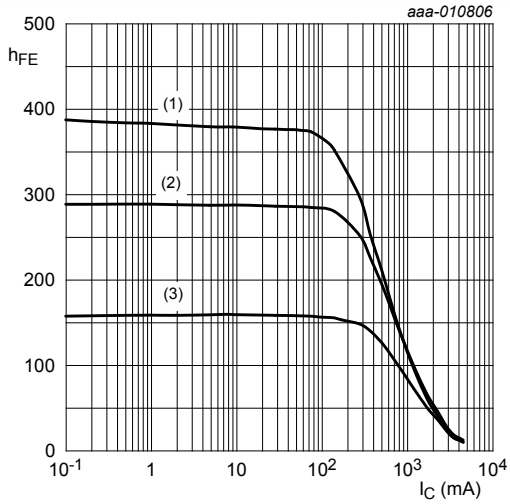




## 10. Characteristics

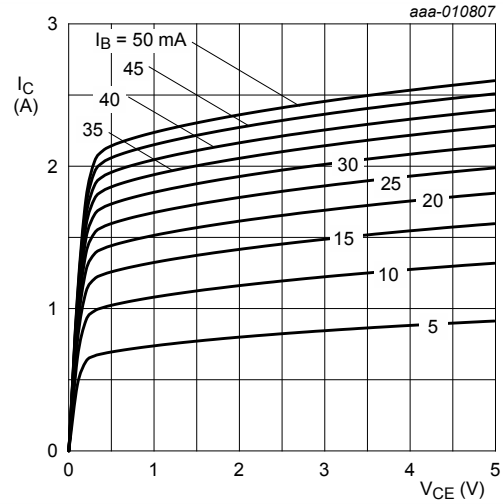
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
		V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 7 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1.5 V; I <sub>C</sub> = 500 mA; T <sub>amb</sub> = 25 °C	100	200	-	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 500 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	150	250	-	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	80	200	-	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 2 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	20	140	-	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 3 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	10	100	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 0.5 A; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	50	75	mV
		I <sub>C</sub> = 2 A; I <sub>B</sub> = 200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	160	300	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	80	150	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	0.92	1	V
		I <sub>C</sub> = 2 A; I <sub>B</sub> = 200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	1.08	1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 0.1 A; T <sub>amb</sub> = 25 °C	-	0.68	0.85	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.05 A; I <sub>Boff</sub> = -0.05 A; T <sub>amb</sub> = 25 °C	-	20	-	ns
t <sub>r</sub>	rise time		-	300	-	ns
t <sub>on</sub>	turn-on time		-	320	-	ns
t <sub>s</sub>	storage time		-	830	-	ns
t <sub>f</sub>	fall time		-	470	-	ns
t <sub>off</sub>	turn-off time		-	1300	-	ns
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	140	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	11	-	pF



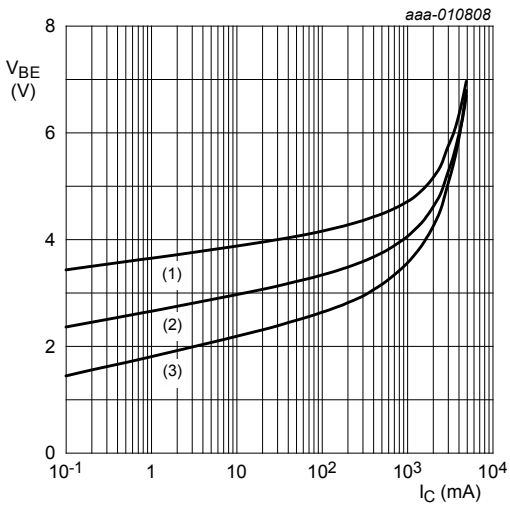
$V_{CE} = 1\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 4. DC current gain as a function of collector current; typical values**



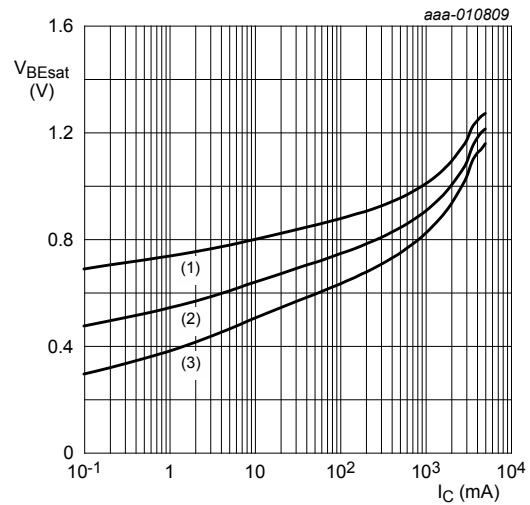
$T_{amb} = 25\text{ }^\circ\text{C}$

**Fig. 5. Collector current as a function of collector-emitter voltage; typical values**



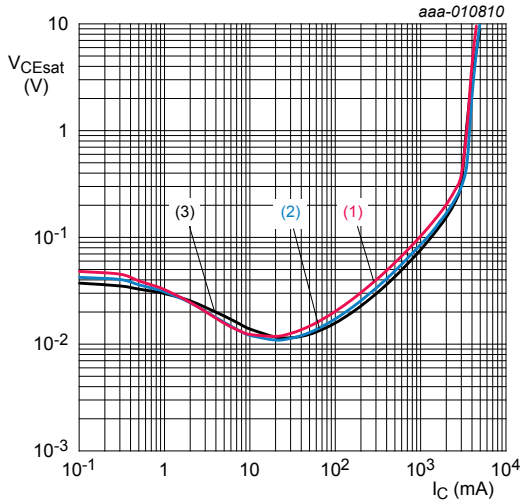
$V_{CE} = 2\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig. 6. Base-emitter voltage as a function of collector current; typical values**



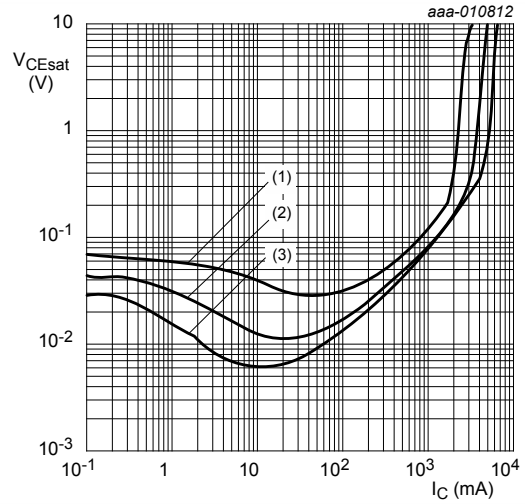
$I_C/I_B = 20$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values**



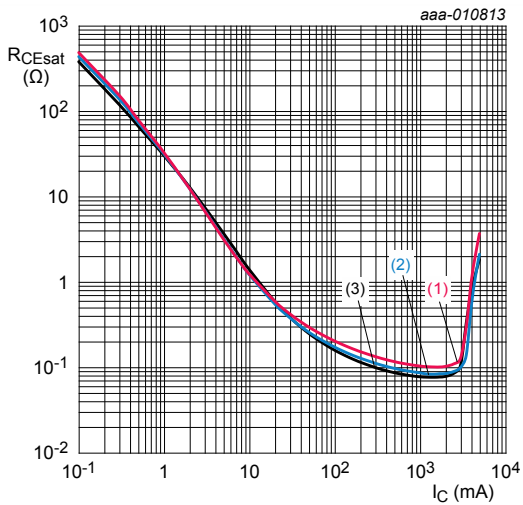
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values**



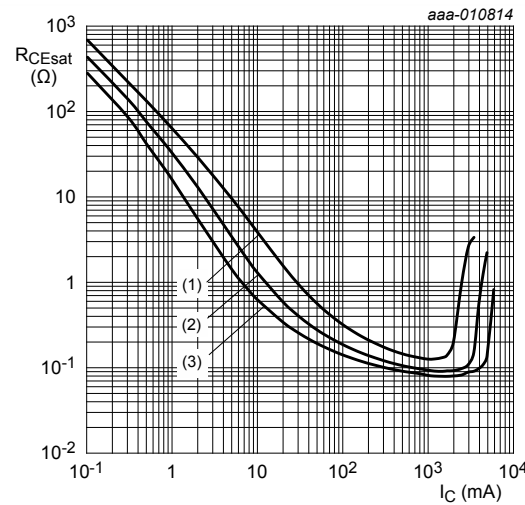
$T_{amb} = 25\text{ }^\circ\text{C}$   
 (1)  $I_C/I_B = 50$   
 (2)  $I_C/I_B = 20$   
 (3)  $I_C/I_B = 10$

**Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values**



$T_{amb} = 25\text{ }^\circ\text{C}$   
 (1)  $I_C/I_B = 50$   
 (2)  $I_C/I_B = 20$   
 (3)  $I_C/I_B = 10$

**Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values**



11. Test information

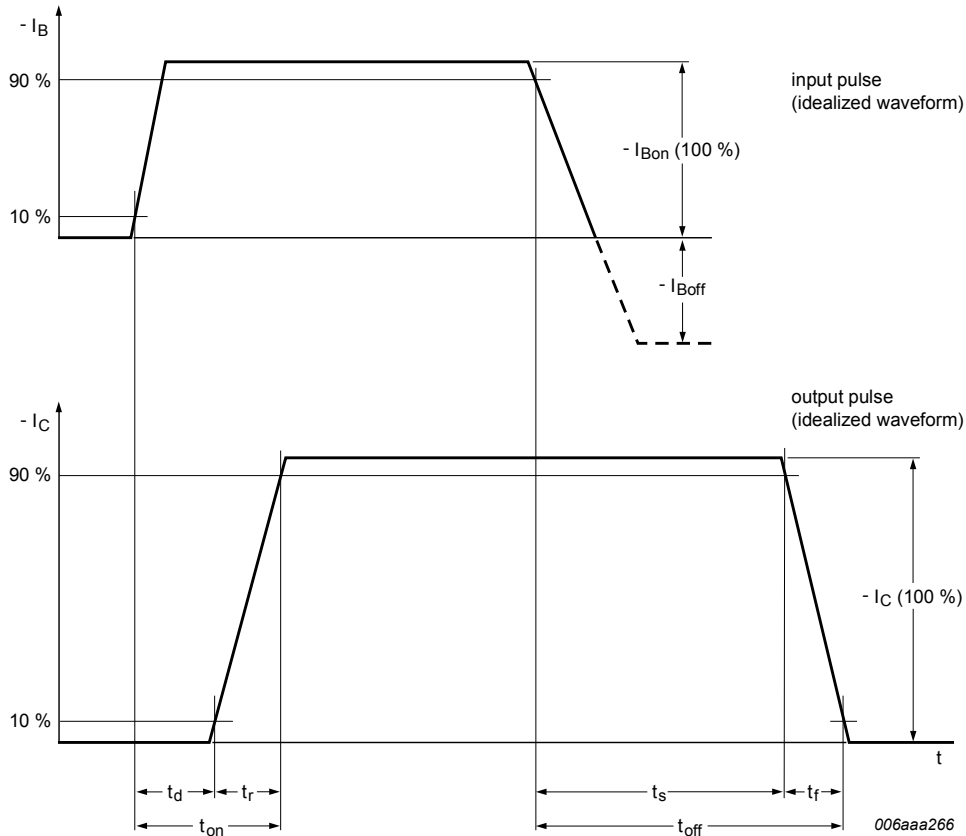


Fig. 12. BISS transistor switching time definition

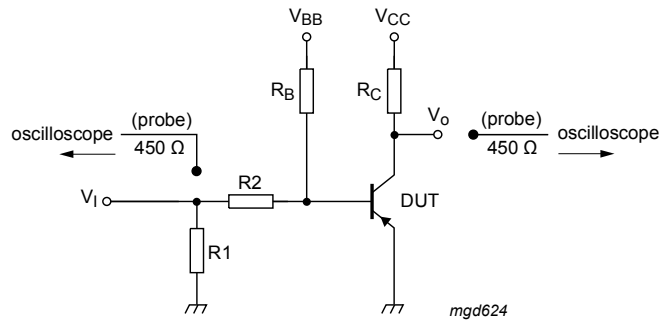


Fig. 13. Test circuit for switching times

## 12. Package outline

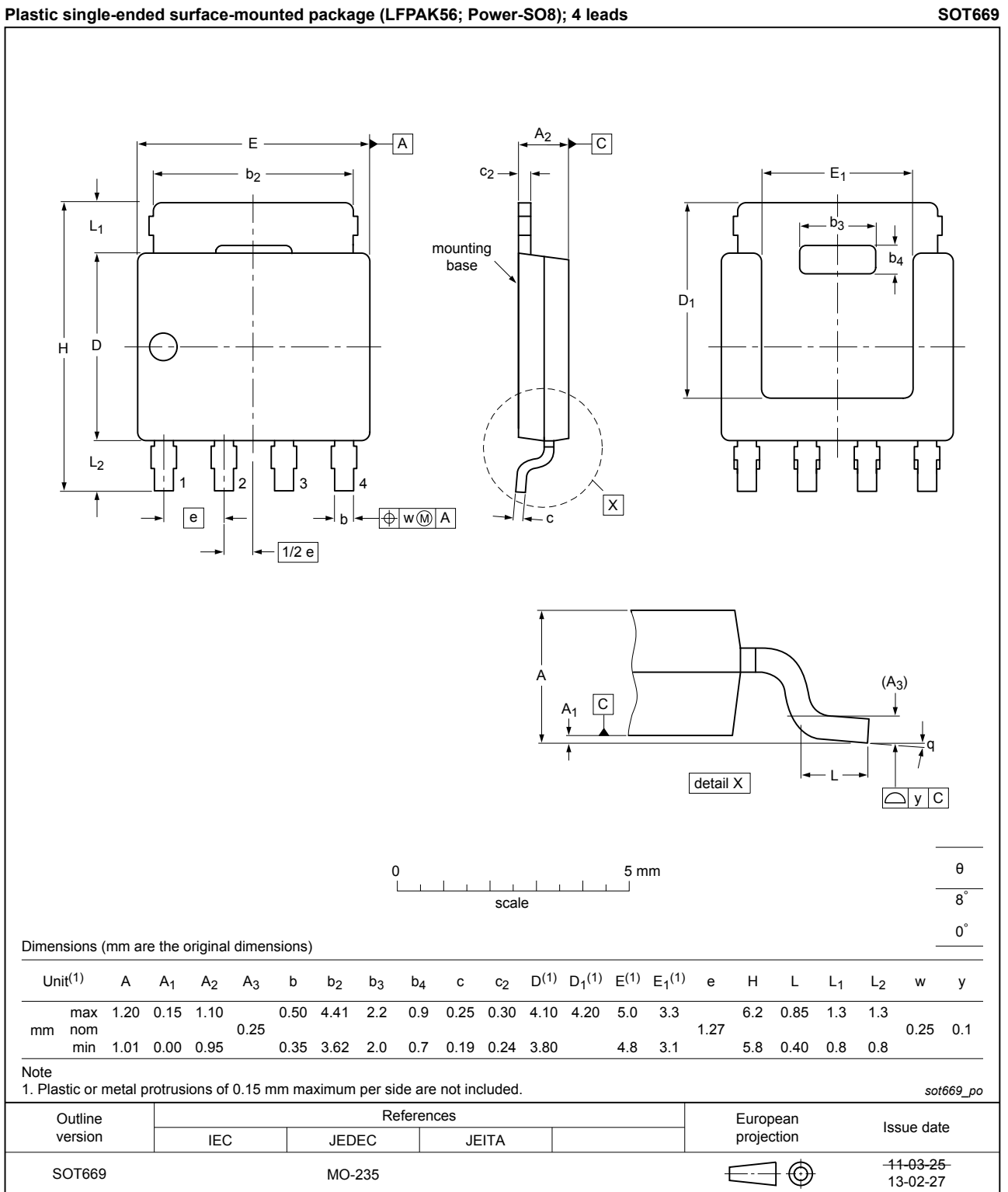


Fig. 14. Package outline LFAK56; Power-SO8 (SOT669)

### 13. Soldering

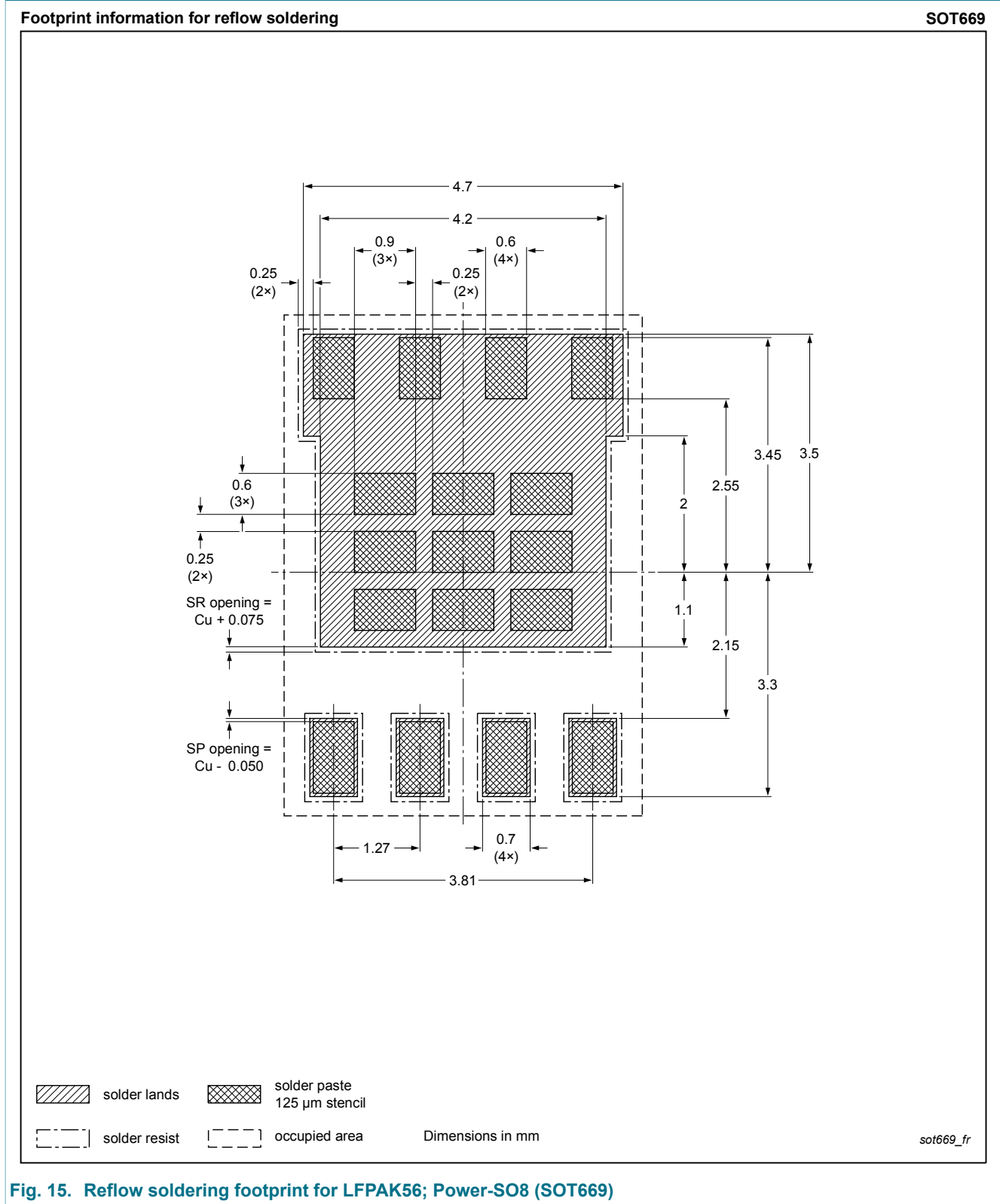


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61002NYC v.1	20140109	Product data sheet	-	-

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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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